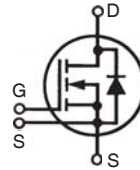


X-Class HiPerFET™ Power MOSFET

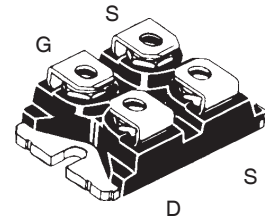
IXFN110N85X

$V_{DSS} = 850V$
 $I_{D25} = 110A$
 $R_{DS(on)} \leq 33m\Omega$

N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Diode



miniBLOC, SOT-227
 E153432



G = Gate
 S = Source
 D = Drain

| Symbol | Test Conditions | Maximum Ratings | |
|---------------|--|-----------------|------------|
| V_{DSS} | $T_J = 25^\circ C$ to $150^\circ C$ | 850 | V |
| V_{DGR} | $T_J = 25^\circ C$ to $150^\circ C$, $R_{GS} = 1M\Omega$ | 850 | V |
| V_{GSS} | Continuous | ± 30 | V |
| V_{GSM} | Transient | ± 40 | V |
| I_{D25} | $T_C = 25^\circ C$ | 110 | A |
| I_{DM} | $T_C = 25^\circ C$, Pulse Width Limited by T_{JM} | 220 | A |
| I_A | $T_C = 25^\circ C$ | 55 | A |
| E_{AS} | $T_C = 25^\circ C$ | 3 | J |
| P_D | $T_C = 25^\circ C$ | 1170 | W |
| dv/dt | $I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$ | 50 | V/ns |
| T_J | | -55 ... +150 | $^\circ C$ |
| T_{JM} | | 150 | $^\circ C$ |
| T_{stg} | | -55 ... +150 | $^\circ C$ |
| V_{ISOL} | 50/60 Hz, RMS $t = 1$ minute | 2500 | V~ |
| | $I_{ISOL} \leq 1mA$ $t = 1$ second | 3000 | V~ |
| M_d | Mounting Torque | 1.5/13 | Nm/lb.in |
| | Terminal Connection Torque | 1.3/11.5 | Nm/lb.in |
| Weight | | 30 | g |

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Isolation Voltage 2500V~
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low $R_{DS(on)}$

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

| Symbol | Test Conditions ($T_J = 25^\circ C$ Unless Otherwise Specified) | Characteristic Values | | |
|--------------|---|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| BV_{DSS} | $V_{GS} = 0V$, $I_D = 3mA$ | 850 | | V |
| $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 8mA$ | 3.5 | | 5.5 V |
| I_{GSS} | $V_{GS} = \pm 30V$, $V_{DS} = 0V$ | | | ± 200 nA |
| I_{DSS} | $V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ C$ | | | 50 μA 5 mA |
| $R_{DS(on)}$ | $V_{GS} = 10V$, $I_D = 55A$, Note 1 | | | 33 m Ω |

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|-------------------------------------|---|--|------|--------------------------|
| | | Min. | Typ. | Max |
| g_{fs} | $V_{DS} = 10\text{V}$, $I_D = 55\text{A}$, Note 1 | 43 | 72 | S |
| R_{Gi} | Gate Input Resistance | | 0.55 | Ω |
| C_{iss} | } $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | | 17 | nF |
| C_{oss} | | | 16 | nF |
| C_{rss} | | | 260 | pF |
| Effective Output Capacitance | | | | |
| $C_{o(er)}$ | Energy related | } $V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$ | 470 | pF |
| $C_{o(tr)}$ | Time related | | 2170 | pF |
| $t_{d(on)}$ | } Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 55\text{A}$ $R_G = 1\Omega$ (External) | | 50 | ns |
| t_r | | | 25 | ns |
| $t_{d(off)}$ | | | 144 | ns |
| t_f | | | 11 | ns |
| $Q_{g(on)}$ | } $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 55\text{A}$ | | 425 | nC |
| Q_{gs} | | | 105 | nC |
| Q_{gd} | | | 225 | nC |
| R_{thJC} | | | | 0.107 $^\circ\text{C/W}$ |
| R_{thCS} | | 0.05 | | $^\circ\text{C/W}$ |

Source-Drain Diode

| Symbol | Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified) | Characteristic Values | | |
|----------|---|-----------------------|------|---------------|
| | | Min. | Typ. | Max. |
| I_S | $V_{GS} = 0\text{V}$ | | | 110 A |
| I_{SM} | Repetitive, Pulse Width Limited by T_{JM} | | | 440 A |
| V_{SD} | $I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1 | | | 1.4 V |
| t_{rr} | } $I_F = 55\text{A}$, $-di/dt = 300\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GS} = 0\text{V}$ | | 205 | ns |
| Q_{RM} | | | 5.5 | μC |
| I_{RM} | | | 54.0 | A |

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

| | | | | | | | | | |
|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

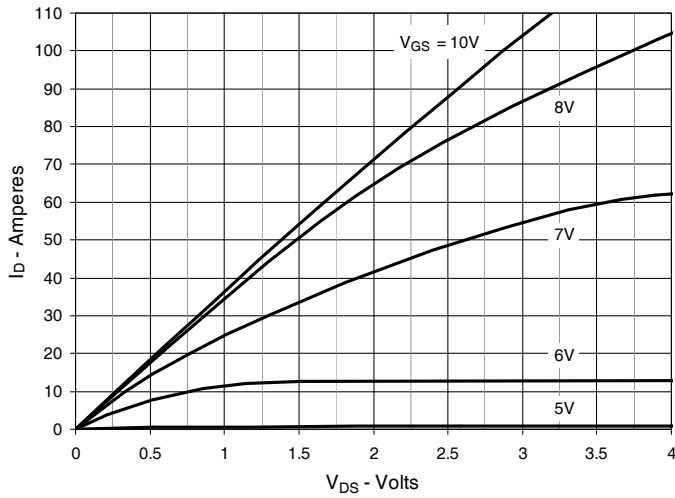


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

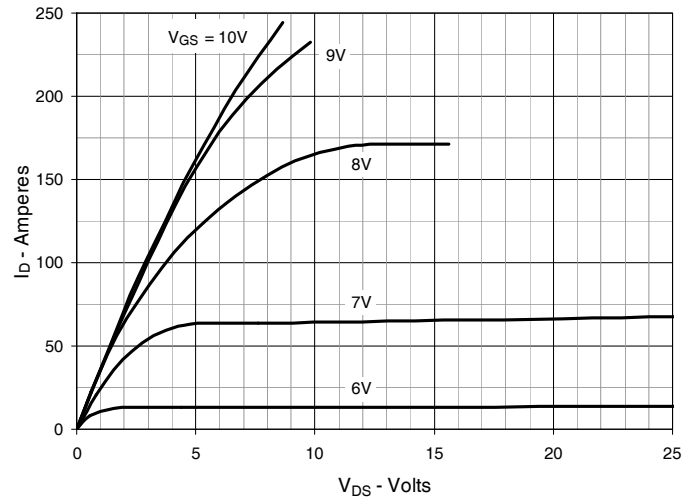


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

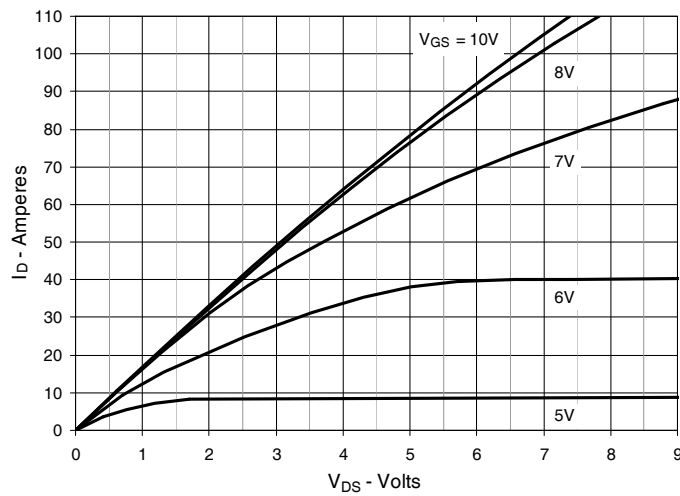


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 55A$ Value vs. Junction Temperature

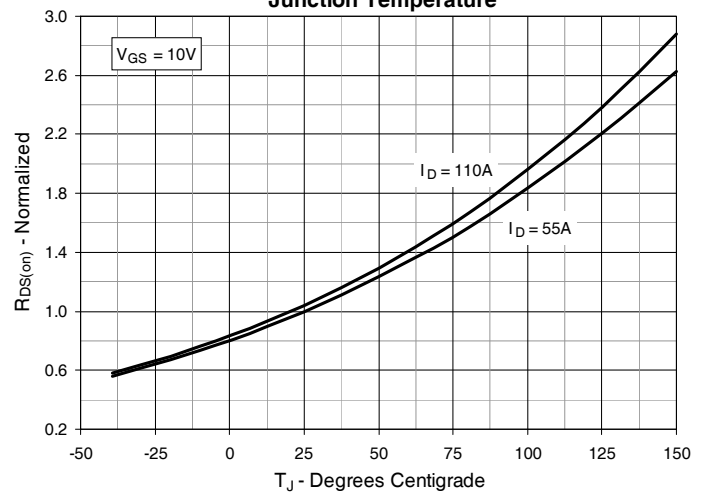


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 55A$ Value vs. Drain Current

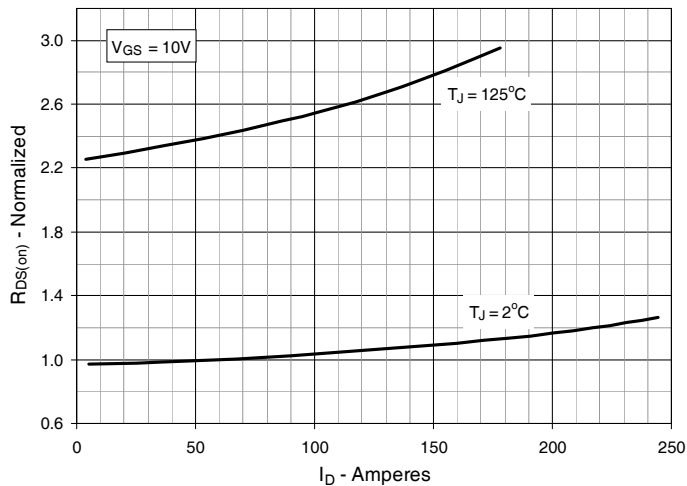


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

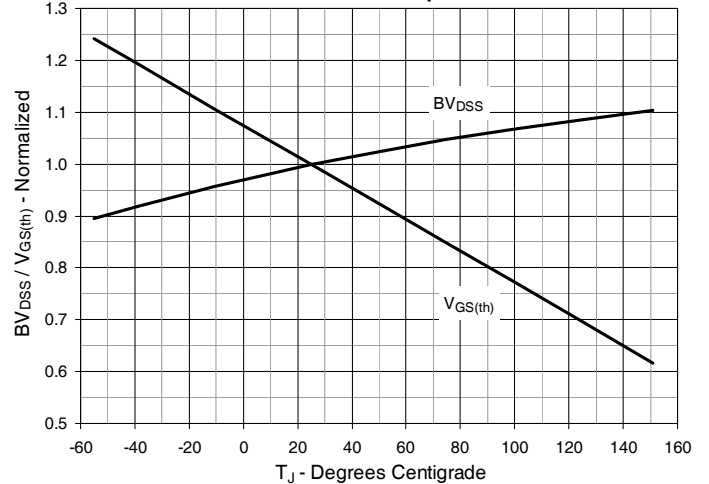


Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

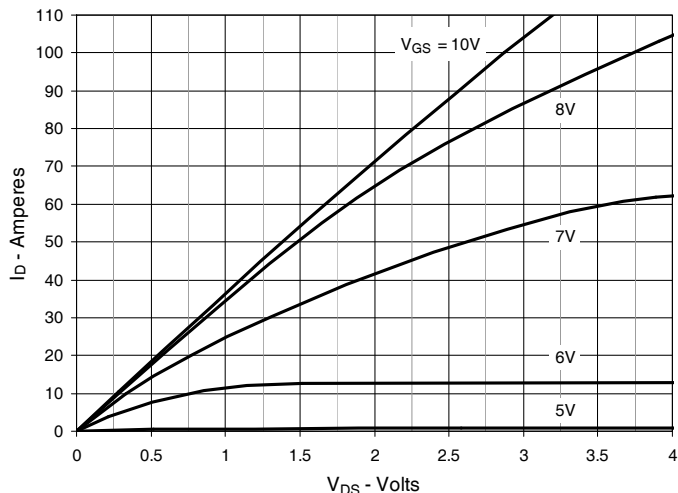


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

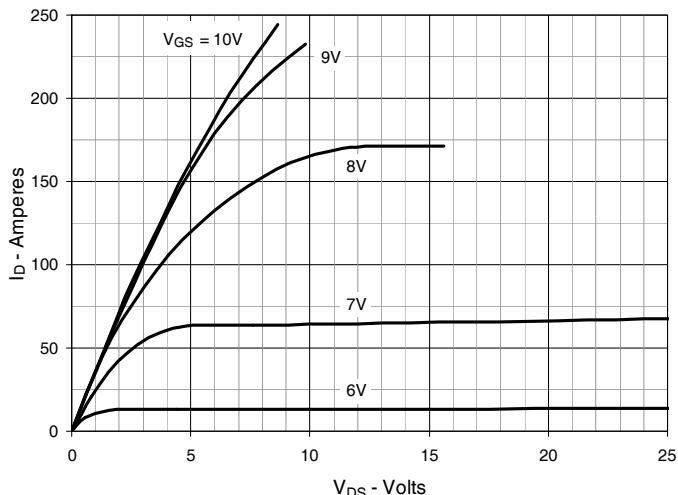


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

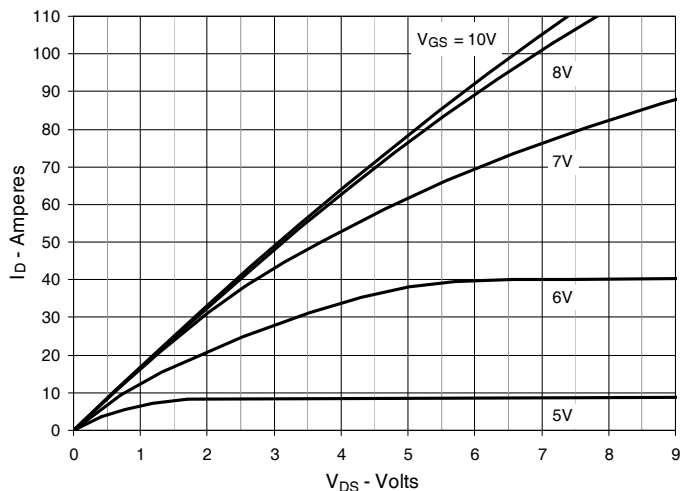


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Junction Temperature

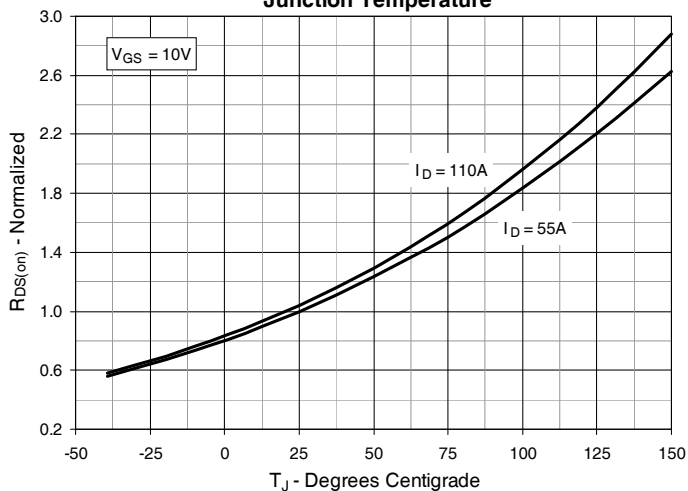


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Drain Current

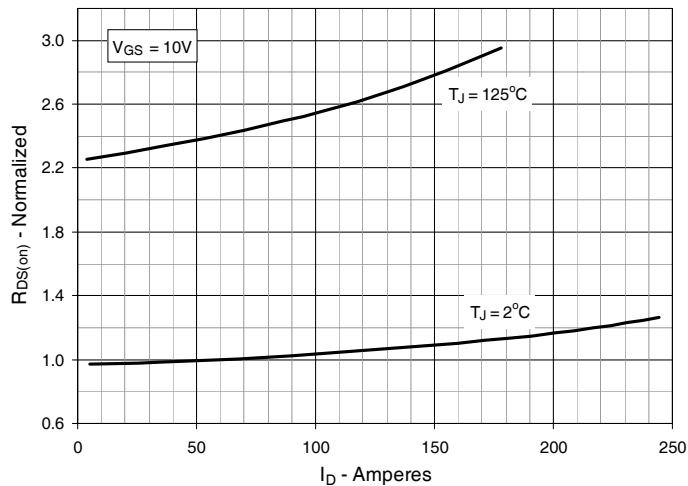


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

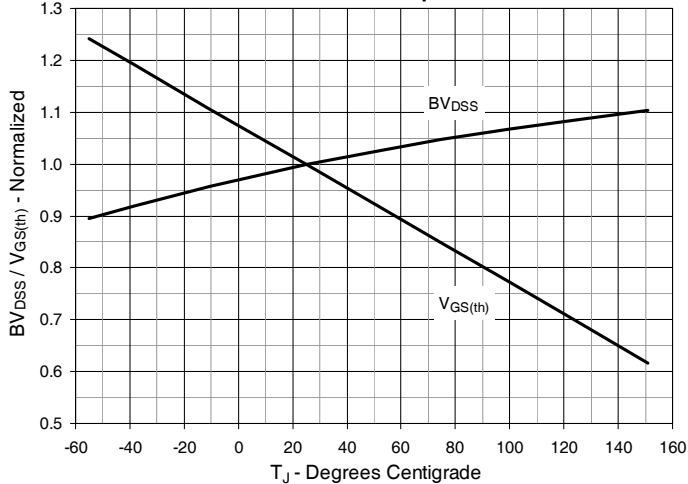


Fig. 13. Output Capacitance Stored Energy

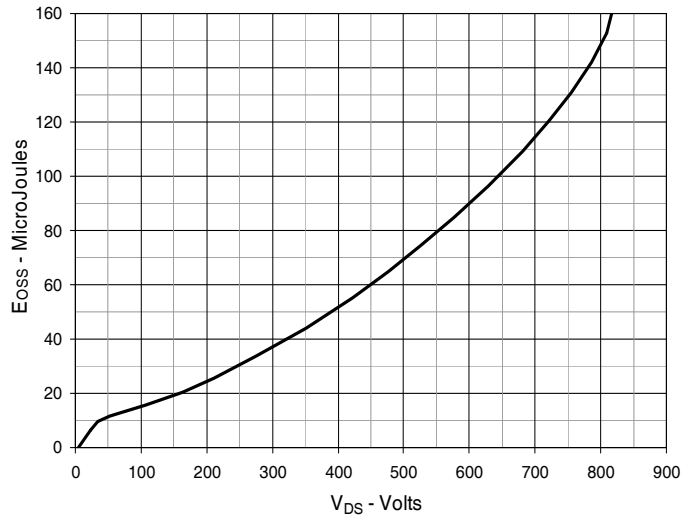


Fig. 14. Forward-Bias Safe Operating Area

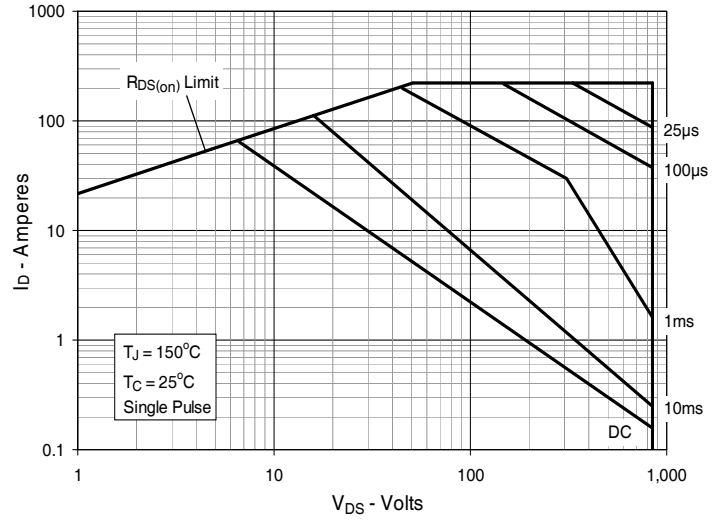
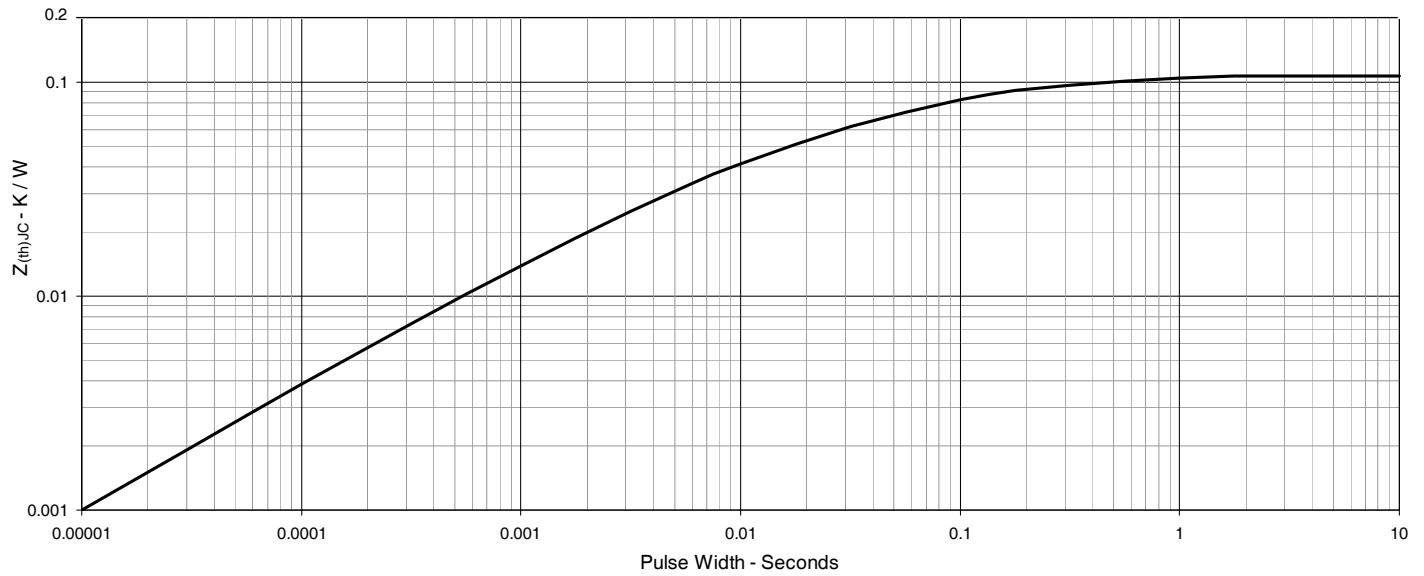
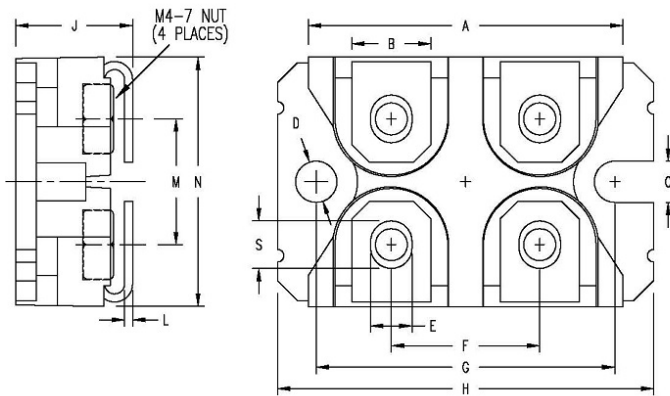
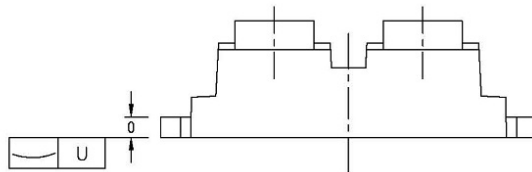


Fig. 15. Maximum Transient Thermal Impedance



SOT-227 Outline


| SYM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 1.224 | 1.260 | 31.10 | 32.00 |
| B | .303 | .327 | 7.70 | 8.30 |
| C | .161 | .173 | 4.10 | 4.40 |
| D | .161 | .173 | 4.10 | 4.40 |
| E | .161 | .173 | 4.10 | 4.40 |
| F | .587 | .598 | 14.90 | 15.20 |
| G | 1.181 | 1.201 | 30.00 | 30.50 |
| H | 1.488 | 1.508 | 37.80 | 38.30 |
| J | .461 | .484 | 11.70 | 12.30 |
| L | .030 | .033 | 0.75 | 0.85 |
| M | .492 | .512 | 12.50 | 13.00 |
| N | .984 | 1.004 | 25.00 | 25.50 |
| O | .075 | .087 | 1.90 | 2.20 |
| S | .181 | .193 | 4.60 | 4.90 |
| U | .000 | .005 | 0.00 | 0.13 |



- NUT MATERIAL:
 STANDARD - Low carbon steel with Ni plating.
 OPTIONAL: - Brass Nut is available.
 PART NUMBER-BN
- ALL METAL SURFACE ARE PRE NI PLATED EXCEPT TRIM AREA.



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